

2-Input NAND **Schmitt-Trigger**

NLV74VHC1G132, NLV74VHC1GT132

The NLV74VHC1G132 / NLV74VHC1GT132 is a single 2-input NAND Schmitt Trigger in tiny footprint packages. The NLV74VHC1G132 has CMOS-level input thresholds while the NLV74VHC1GT132 has TTL-level input thresholds.

The input structures provide protection when voltages up to 5.5 V are applied, regardless of the supply voltage. This allows the device to be used to interface 5 V circuits to 3 V circuits. Some output structures also provide protection when $V_{CC} = 0 \text{ V}$ and when the output voltage exceeds V_{CC}. These input and output structures help prevent device destruction caused by supply voltage - input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- Designed for 2.0 V to 5.5 V V_{CC} Operation
- 3.6 ns t_{PD} at 5 V (typ)
- Inputs/Outputs Over-Voltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Source/Sink 8 mA at 3.0 V
- Available in SC-88A and TSOP-5 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

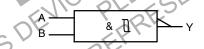


Figure 1. Logic Symbol

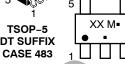
MARKING DIAGRAMS



DF SUFFIX CASE 419A









= Specific Device Code Date Code* = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 7 of this data sheet.

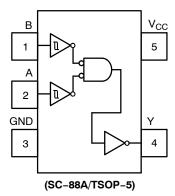


Figure 2. Pinout (Top View)

PIN ASSIGNMENT (SC-88A/TSOP-5)

				iiput	Output
Pin	Function		Α	В	YC
1	В		L	L	, (H)
2	Α		L	н	W H
3	GND	1	Н		Н
4	Y		Н	H A	L\
5	V _{CC}			COM	10/
HISDEVIC	SEIS NOTE PLEASE PRESENTE	RECONNER	OUR ORINI ORINI	ORMA	

FUNCTION TABLE

Inp	Output			
Α	В	YS		
L	L	H		
L	Н	NH		
Н	27/1/2	Н		
H	H	L\		

MAXIMUM RATINGS

Symbol	C	haracterist	ics	Value	Unit
V _{CC}	DC Supply Voltage			-0.5 to +7.0	V
V _{IN}	DC Input Voltage			-0.5 to +7.0	V
V _{OUT}	DC Output Voltage	1Gxx		-0.5 to V _{CC} + 0.5	V
		-0.5 to V _{CC} + 0.5 -0.5 to +7.0 -0.5 to +7.0			
I _{IK}	DC Input Diode Current		V _{IN} < GND	-20	mA
I _{OK}	DC Output Diode Current	1Gxx	$V_{OUT} > V_{CC}$, $V_{OUT} < GND$	±20	mA
		1GTxx	V _{OUT} < GND	-20	
I _{OUT}	DC Output Source/Sink Current	±25	mA		
I _{CC} or I _{GND}	DC Supply Current per Supply Pir	±50	mA		
T _{STG}	Storage Temperature Range			-65 to +150	ĵ
T _L	Lead Temperature, 1 mm from Ca	se for 10 se	ecs	260	°C
T_J	Junction Temperature Under Bias			+150	°C
θ_{JA}	Thermal Resistance (Note 2)		SC-88A TSOP-5	377 320	°C/W
P _D	Power Dissipation in Still Air		SC-88A TSOP-5	332 390	mW
MSL	Moisture Sensitivity	Moisture Sensitivity			
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-	
V _{ESD}	ESD Withstand Voltage (Note 3)		Human Body Model Charged Device Model	2000 1000	V
I _{Latchup}	Latchup Performance (Note 4)		Oh. L 141	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Applicable to devices with outputs that may be tri-stated.
- Applicable to devices with outputs that may be at stated.
 Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
 HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22 EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A. Tested to EIA/JESD78 Class II.
- 4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	CI	Min	Max	Unit	
V _{CC}	Positive DC Supply Voltage			5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage	1Gxx	0	V _{CC}	V
		1GTxx Active-Mode (High or Low State) Tri-State Mode Power-Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 3.0 V to 3.6 V V _{CC} = 4.5 V to 5.5 V	0 0	No Limit No Limit	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (NLV74VHC1G132)

		Test	v _{cc}	٦	Γ _A = 25°	С	-40°C ≤ T	A ≤ 85°C	-55°C ⊴ T ₄	\	
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{T+}	Positive Input Threshold Voltage		3.0 4.5 5.5	1.2 1.75 2.15	2.0 3.0 3.6	2.2 3.15 3.85	-	2.2 3.15 3.85	- - -	2.2 3.15 3.85	V
V _{T-}	Negative Input Threshold Voltage		3.0 4.5 5.5	0.9 1.35 1.65	1.5 2.3 2.9	1.9 2.75 3.35	0.9 1.35 1.65	eni	0.9 1.35 1.65	1 1 1	V
V _H	Hysteresis Voltage		3.0 4.5 5.5	0.30 0.40 0.50	0.57 0.67 0.74	1,20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	٧
V _{OH}	High-Level Output Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OH} = -50 \mu A \\ &I_{OH} = -50 \mu A \\ &I_{OH} = -50 \mu A \\ &I_{OH} = -4 m A \\ &I_{OH} = -8 m A \end{aligned}$	2.0 3.0 4.5 3.0 4.5	1.9 2.9 4.4 2.58 3.94	2.0 3.0 4.5)P.	1.9 2.9 4.4 2.48 3.80	- - -	1.9 2.9 4.4 2.34 3.66		>
V _{OL}	Low-Level Output Voltage	$\begin{aligned} V_{IN} &= V_{IH} \text{ or } V_{IL} \\ I_{OL} &= 50 \mu\text{A} \\ I_{OL} &= 50 \mu\text{A} \\ I_{OL} &= 50 \mu\text{A} \\ I_{OL} &= 4 m\text{A} \\ I_{OL} &= 8 m\text{A} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	- - -	0.0 0.0 0.0 - -	0.1 0.1 0.1 0.36 0.36	11111	0.1 0.1 0.1 0.44 0.44	1 1 1	0.1 0.1 0.1 0.52 0.52	V
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	2.0 to 5.5	_	_	±0.1	_	±1.0	-	±1.0	μΑ
l _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V	0.0	-	-	1.0	_	10	-	10	μΑ
Icc	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5	_	-	1.0	_	20	-	40	μΑ

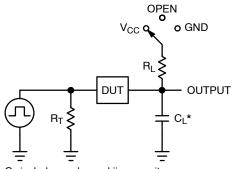
DC ELECTRICAL CHARACTERISTICS (NLV74VHC1GT132)

		Test	V _{CC}	1	_A = 25°	С	-40°C ≤ 1	Γ _A ≤ 85°C	-55°C ≤ T	_∆ ≤ 125°C	
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{T+}	Positive Input Threshold Voltage		3.0 4.5 5.5	1.2 1.58 1.79	1.4 1.74 1.94	1.6 2.0 2.1	- - -	1.6 2.0 2.1	-	1.6 2.0 2.1	٧
V _{T-}	Negative Input Threshold Voltage		3.0 4.5 5.5	0.35 0.5 0.6	0.76 1.01 1.13	0.93 1.18 1.29	0.35 0.5 0.6	- - -	0.35 0.5 0.6	- - -	٧
V _H	Hysteresis Voltage		3.0 4.5 5.5	0.30 0.40 0.50	0.64 0.73 0.81	1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	٧
V _{OH}	High-Level Output Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -50 \mu\text{A} \\ &I_{OH} = -4 m\text{A} \\ &I_{OH} = -8 m\text{A} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	1.9 2.9 4.4 2.58 3.94	2.0 3.0 4.5 -		1.9 2.9 4.4 2.48 3.80	- - - -	1.9 2.9 4.4 2.34 3.66		V
V _{OL}	Low-Level Output Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 4 \text{ mA} \\ &I_{OL} = 8 \text{ mA} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	- - - -	0.0 0.0 0.0 - -	0.1 0.1 0.1 0.36 0.36	- - -	0.1 0.1 0.1 0.44 0.44	NOE!	0.1 0.1 0.1 0.52 0.52	V
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	2.0 to 5.5	-		±0.1	rO.	±1.0	Jan 1	±1.0	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0		-	1.0	D-\0	540	10.	10	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5		1/2	7.0	UPC	20	-	40	μΑ
Ісст	Increase in Quiescent Supply Current per Input Pin	One Input: V _{IN} = 3.4 V; Other Input at V _{CC} or GND	5.5	700	VC.	1.35	IM	1.5	-	1.65	mA

		19,	5	(\\ \ \	A = 25°	С	-40°C ≤ 1	T _A ≤ 85°C	-55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Conditions	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} ,	Propagation Delay,	C _L = 15 pF	3.0 to 3.6	-	4.6	11.9	_	14.0	-	16.1	ns
t _{PHL}	A to Y (Figures 3 and 4)	C _L = 50 pF		-	6.1	15.4	_	17.5	_	19.6	
	المالة	C _L = 15 pF	4.5 to 5.5	-	3.6	7.7	_	9.0	_	10.3	
~	1	C _L = 50 pF		-	4.3	9.7	_	11.0	-	12.3	
C _{IN}	Input Capacitance			-	4.0	10	_	10	_	10	pF
C _{OUT}	Output Capacitance	Output in High Impedance State		-	6.0	-	-	-	-	-	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 5)	8.0	рF

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \cdot C_{PD}$ is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



Test	Switch Position	C _L , pF	R_L, Ω
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table	Χ
t _{PLZ} / t _{PZL}	V _{CC}		1 k
t _{PHZ} / t _{PZH}	GND		1 k

X = Don't Care

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$ f = 1 MHz

Figure 3. Test Circuit

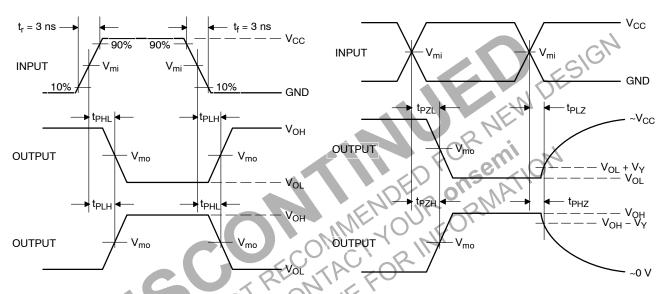


Figure 4. Switching Waveforms

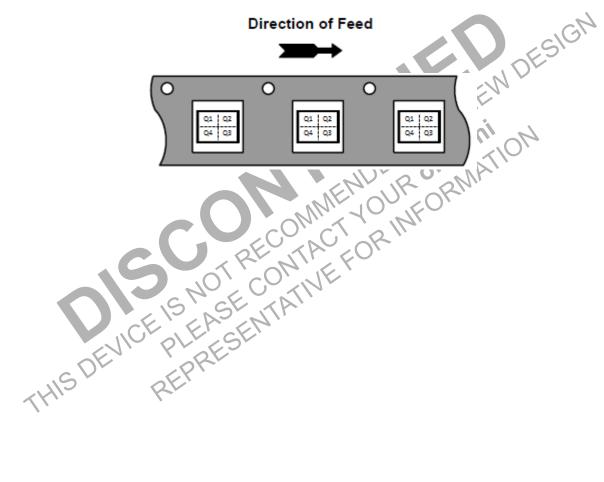
	110 -1 E GF	V _{mo}		
V _{CC} , V	V _{mi} , v	t _{PLH} , t _{PHL}	t_{PZL} , t_{PLZ} , t_{PZH} , t_{PHZ}	V _Y , V
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3

ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
M74VHC1G132DFT2G-L22038	SC-88A	VD	Q4	3000 / Tape & Reel
NLVVHC1G132DFT1G*	SC-88A	VD	Q2	3000 / Tape & Reel
NLVVHC1G132DFT2G*	SC-88A	VD	Q4	3000 / Tape & Reel
M74VHC1G132DTT1G	TSOP-5	VD	Q4	3000 / Tape & Reel
NLVVHC1G132DTT1G*	TSOP-5	VD	Q4	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PIN 1 ORIENTATION IN TAPE AND REEL



^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.







SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

DATE 11 APR 2023

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETERS
- OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

DIM	MILLIMETERS					
ואונת	MIN.	N□M.	MAX.			
А	0.80	0.95	1.10			
A1			0.10			
A3	0.20 REF					
b	0.10	0.20	0.30			
C	0.10		0.25			
D	1.80	2.00	2,20			
Е	2.00	2.10	2.20			
E1	1.15	1.25	1.35			
е		0.65 BSI				
L	0.10	0.15	0.30			

- 419A-01 DBSDLETE, NEW STANDARD 419A-02
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS,

	L → -	
<u> </u>	0.50	5

5X b

◆ 0.2 M B M

RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

5. COLLECTOR

GENERIC MARKING DIAGRAM*



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

STYLE 1: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE	STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1	STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2	STYLE 5: PIN 1. CATHODE 2. COMMON ANODE 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4
STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE 1	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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DESCRIPTION:	SC-88A (SC-70-5/SOT-35	53)	PAGE 1 OF 1

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5. COLLECTOR 2/BASE 1



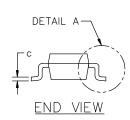
TSOP-5 3.00x1.50x0.95, 0.95P **CASE 483**

ISSUE P

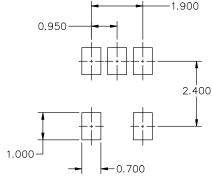
DATE 01 APR 2024

NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME 1. Y14.5-2018.
- 2.
- ALL DIMENSION ARE IN MILLIMETERS (ANGLES IN DEGREES). MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. 3. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION D.
- OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.



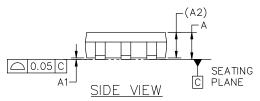
DIM	MILLIMETERS		
ואוט	MIN.	NOM.	MAX.
Α	0.900	1.000	1.100
A1	0.010	0.055	0.100
A2	0.950 REF.		
b	0.250	0.375	0.500
С	0.100	0.180	0.260
D	2.850	3.000	3.150
Е	2.500	2.750	3.000
E1	1.350	1.500	1.650
е	0.950 BSC		
L	0.200	0.400	0.600
Θ	0.	5°	10°

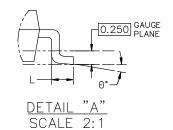


RECOMMENDED MOUNTING FOOTPRINT*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTE 5 В Ė1 PIN 1 **IDENTIFIER** ΙAŀ TOP VIEW





GENERIC MARKING DIAGRAM*





= Date Code

= Pb-Free Package

Analog Discrete/Logic XXX = Specific Device Code

XXX = Specific Device Code = Assembly Location

= Year W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

М

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMB	ED.
DOCUMENT NUMB	En:

98ARB18753C

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DESCRIPTION:

TSOP-5 3.00x1.50x0.95, 0.95P

PAGE 1 OF 1

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